IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In resistant Saxler et al.

Saxler et al.

10/617,843

Filed: July 11, 2003

Group Art Unit: 2811
Examiner: To Be Assigned
Confirmation No.: 7985

For: N

DEC 1 2 2003

NITRIDE-BASED TRANSISTORS AND METHODS OF FABRICATION THEREOF

USING NON-ETCHED CONTACT RECESSES

Date: December 10, 2003

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT (INTERNATIONAL SEARCH REPORT)

Sir:

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Attached is a Supplemental Form PTO-1449 listing documents cited in the International Search Report for the corresponding International Application Number PCT/US03/21895. Each document listed on the attached PTO-1449 was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement. A copy of each document, including the Search Report, is enclosed. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and MPEP § 609.

No fee is believed due; however, the Commissioner is hereby authorized to charge any deficiency or credit any refund to Deposit Account No. 50-0220.

Respectfully submitted,

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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on December 10, 2003.

Candi L. Riggs

	Pate	U.S. Department of the transfer of the transfe	Office	Attorney Docket Number 5308-248			Serial No. 10/617,843	
DEC 1 2 2003	S (L	OCUMENTS CITE Use several sheets if	necessary)					
TRADELLINE S					Applicants: Adam William Saxler et al.			
					Filing Date: July 11, 2003			Group 2811
		U. S. P	ATENTS & I	PATENT APPL	ICATION PUB	LICATIONS		
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	5	WO 01/57929	8/9/01	РСТ		H01L	29/778	
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